

Appl. No. 10/765,808
Amdt. Dated 10/02/2009
Response to Office Action of 06/03/2009

Attorney Docket No.: N1085-00256
[TSMC2003-0899]

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application:

1 1. (Currently Amended) A plasma etching apparatus comprising a chuck adapted to
2 retain a substrate thereover and hardware that is formed of a material that includes
3 oxygen impregnated therein such that said oxygen is released when an etching
4 operation is carried out, wherein said hardware comprises a focus ring maintained at a
5 temperature less than a temperature of said substrate while an etching operation is
6 carried out upon said substrate, and at least only a single portion of said focus ring
7 extending inwardly past a peripheral edge of said chuck, said single portion extending
8 substantially continuously ~~extends~~ directly underneath a peripheral portion of said chuck
9 that extends directly underneath a peripheral portion of said substrate.

1 2. (Previously Presented). The plasma etching apparatus as in claim 1, wherein
2 said chuck is substantially circular and said focus ring peripherally surrounds said
3 chuck.

1 3. (Currently Amended) The plasma etching apparatus as in claim 2, wherein said
2 focus ring comprises a lower focus ring and further comprising an upper focus ring, ~~at~~
3 ~~least a portion of said lower focus ring substantially continuously extending below a~~
4 ~~peripheral portion of said chuck.~~

1 4. (Original) The plasma etching apparatus as in claim 1, wherein said chuck
2 comprises an electrostatic chuck.

1 5. (Original) The plasma etching apparatus as in claim 1, wherein said hardware
2 comprises a focus ring composed primarily of quartz.

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1 6. (Original) The plasma etching apparatus as in claim 1, wherein said hardware
2 comprises a focus ring formed of a ceramic.

1 7-9. (Cancelled).

1 10. (Currently Amended) The plasma etching apparatus as in claim [[9]] 1, wherein
2 said chuck comprises an electrostatic chuck and said substrate comprises a
3 semiconductor substrate.

1 11. (Currently Amended) The plasma etching apparatus as in claim [[9]] 1, wherein
2 said chuck comprises an electrostatic chuck and said focus ring maintains contact with
3 said electrostatic chuck and said electrostatic chuck is cooled during said etching
4 operation.

1 12. (Currently Amended) The plasma etching apparatus as in claim 11, wherein said
2 focus ring is disposed peripherally around said substrate and ~~includes a~~ said single
3 ~~portion that~~ rests on an annular landing section of said electrostatic chuck.

1 13-30. (Cancelled)

1 31. (Currently Amended) The plasma etching apparatus as in claim [[30]] 1, wherein
2 said chuck comprises an electrostatic chuck.

1 32. (Currently Amended) The plasma etching apparatus as in claim [[31]] 1, wherein
2 said chuck is disposed within an etching chamber and further comprising said etching
3 chamber containing therein further hardware formed of said material that includes
4 oxygen-impregnated ~~material~~ therein.

1 33. (Cancelled)